

A 300ksps, Single-supply, Low-Power 12-Bit Serial-output ADC

FEATURES

- ♦ Alternate Source for MAX1285 and higher-speed upgrade to MAX1240 and MAX1241
- ♦ Single-Supply Operation: +2.7V to +3.6V
- ♦ DNL & INL: ±1LSB (max)
- ♦ 300ksps Sampling Rate
- Low Conversion-Mode Supply Current: 2.5mA @ 300ksps
- ♦ Low Supply Current in Shutdown: 2µA
- ♦ Internal Track-and-Hold
- ♦ Internal +2.5V Reference
- ♦ SPI®/QSPI™/MICROWIRE™ 3-Wire Serial-Interface¹
- ♦ 8-Pin SOIC Package

APPLICATIONS

Process Control and Factory Automation
Data and Low-frequency Signal Acquisition
Portable Data Logging
Pen Digitizers & Tablet Computers
Medical Instrumentation
Battery-powered Instruments

¹ SPI and QSPI are trademarks of Motorola, Inc. MICROWIRE is a trademark of National Semiconductor Corporation.

DESCRIPTION

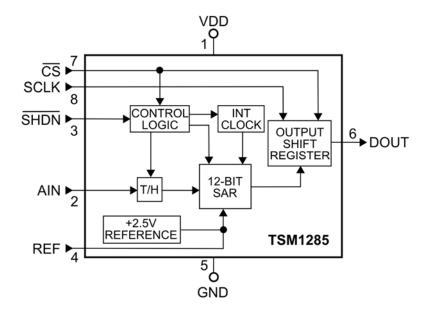
The TSM1285 – a single-supply, single-channel, 12-bit analog-to-digital converter (ADC) - is an alternate source for the MAX1285 and a higher-speed upgrade to the MAX1240 and MAX1240 ADCs. The TSM1285 combines a high-bandwidth track-and-hold (T/H), a high-speed serial digital interface, an internal +2.5V reference, and low conversion-mode power consumption. The TSM1285 operates from a single +2.7V to+3.6V supply and draws less than 2.5mA at 300ksps.

Connecting directly to any SPI, QSPI, MICROWIRE™ microcontrollers and other interface-compatible computing devices, the TSM1285's 3-wire serial interface is easy to use and doesn't require separate, external logic. An external serial-interface clock controls the TSM1285's conversion process and its output shift register operation.

In PCB-space-conscious, low-power remote-sensor and data-acquisition applications, the TSM1285 is an excellent choice for its low-power, ease-of-use, and small-package-footprint attributes.

The TSM1285BC is fully specified over the 0°C to +70°C temperature range. TSM1285BE is fully specified over the -40°C to +85°C temperature range. Both products are available in a 8-pin SOIC package.

FUNCTIONAL BLOCK DIAGRAM





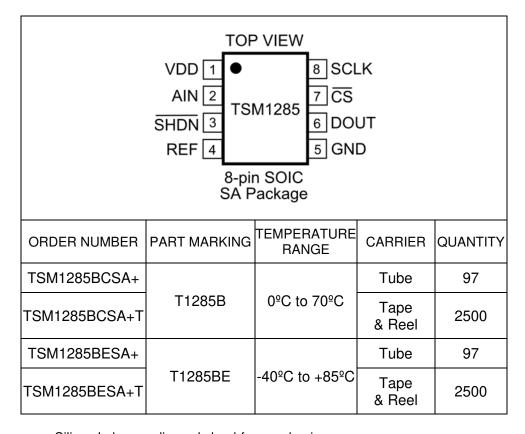
ABSOLUTE MAXIMUM RATINGS

V _{DD} to GND	0.3V to +6V
AIN to GND	0.3V to $(V_{DD} + 0.3V)$
REF to GND	0.3V to $(V_{DD} + 0.3V)$
Digital Inputs to GND	0.3V to $(V_{DD} + 0.3V)$
DOUT to GND	0.3V to $(V_{DD} + 0.3V)$
DOUT Current	±25mA
Continuous Power Dissipation ($T_A = +7$	70°C):
8-Pin SOIC (Derate 5.88mW/°C ab	ove +70°C) 471mW

Operating Temperature Ranges:	
TSM1285BC	0°C to +70°C
TSM1285BE	40°C to +85°C
Storage Temperature Range	60°C to +150°C
Lead Temperature (Soldering, 10s)	+300°C
Soldering Temperature (Reflow)	

Electrical and thermal stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to any absolute maximum rating conditions for extended periods may affect device reliability and lifetime.

PACKAGE/ORDERING INFORMATION



Lead-free Program: Silicon Labs supplies only lead-free packaging.

Consult Silicon Labs for products specified with wider operating temperature ranges.

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ELECTRICAL SPECIFICATIONS

 V_{DD} = +2.7V to +3.6V; f_{SCLK} = 4.8MHz, 50% duty cycle, 16 clocks/conversion cycle, 300ksps; 4.7 μ F capacitor at REF; T_A = -40 $^{\circ}$ C to +85 $^{\circ}$ C, unless otherwise noted. Typical values apply at T_A = +25 $^{\circ}$ C.

Resolution	PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Relative Accuracy INL See Note 2	DC ACCURACY (See Note 1)					•	
Differential Nonlinearity DNL No missing codes over temperature 1.1 0 LSB	Resolution			12			Bits
See Note 3 16.0 LSB See Note 3 LSB	Relative Accuracy	INL	See Note 2			±1.0	LSB
Offset Error ZE Gain Error GE GE See Note 3 ±6.0 LSB LSB LSB Gain-Error Temperature Coefficient TCGE ±1.6 LSB pmm²C Gain Error Temperature Coefficient TCGE ±1.6 ppm²C		DNL	No missing codes over temperature			±1.0	LSB
Gain-Error GE See Note 3 ±6.0 LSB		ZE				±6.0	LSB
DYNAMIC SPECIFICATIONS (I _{IN} = 75kHz sine wave, 2.5V _{PP} , f _{SAMPLE} = 300ksps, f _{SCLK} = 4.8MHz) Signal-to-Noise SINAD 70		GE	See Note 3			±6.0	LSB
Signal-to-Noise Plus Distortion Ratio THD Including the 5th harmonic -80 dB	Gain-Error Temperature Coefficient	TCGE			±1.6		ppm/°C
Plus Distortion Ratio SINAU GB	DYNAMIC SPECIFICATIONS (f _{IN} = 7	5kHz sine wa	ve, $2.5V_{PP}$, $f_{SAMPLE} = 300ksps$, $f_{SCLK} = 4.8MHz$	<u>z</u>)			
Total Harmonic Distortion		SINAD			70		dB
Spurious-Free Dynamic Range SFDR		TUD	In alterding the Cale harmonic		00		٩D
Intermodulation Distortion			including the 5th narmonic				
Full-Linear Bandwidth	, ,		f 70111- f 77111-				
Full-Linear Bandwidth FLBW SINAD > 68dB 250 kHz							_
CONVERSION RATE toonv See Note 4 3.3 μs Track/Hold Acquisition Time taco 9 625 ns Aperture Delay tab 10 ns Aperture Uitter tab 0.5 4.8 MHz Duty Cycle 40 60 % ANALOG INPUT (AIN) 0 2.5 V Input Voltage Range V _{IN} 0 2.5 V Input Capacitance C _{RNA} 0 0 2.5 V Input Capacitance C _{RNA} 0 0 2.5 V Input Capacitance C _{RNA} 10 pF INTERNAL REFERENCE REF Output Voltage VREF 2.48 2.50 2.52 V REF Output Tempco TCVREF 15 mA nA nEF Output Tempco 15 mA Load Regulation See Note 5; 0 to 0.75mA output load 0.1 2.0 mV/mA Load Regulation See Note 5; 0 to 0.75mA output load 0.1 2.0 <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td>							
Conversion Time tconv See Note 4 3.3		FLBW	SINAD > 680B		250		KHZ
Track/Hold Acquisition Time			To N. 4	1 00	ı		
Aperture Delay			See Note 4	3.3		005	
Aperture Jitter					40	625	
Serial Clock Frequency							†
Duty Cycle					< 50		
ANALOG INPUT (AIN) Input Voltage Range V _{IN} 0 2.5 V Input Capacitance C _{INA} 10 pF		t _{SCLK}					
Input Voltage Range				40		60	%
$ \begin{array}{ c c c c c } \hline \text{Input Capacitance} & C_{\text{INA}} & 10 & pF \\ \hline \textbf{INTERNAL REFERENCE} \\ \hline \textbf{REF Output Voltage} & VREF & 2.48 & 2.50 & 2.52 & V \\ \hline \textbf{REF Short-Circuit Current} & T_A = +25^{\circ}\text{C} & 15 & mA \\ \hline \textbf{REF Output Tempco} & TCVREF & 5ee Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{DIGITAL INPUTS (SCLK, \overline{\textbf{CS}}, \overline{\textbf{SHDN}})} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{DIGITAL OUTPUT (DOUT)} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & C_{\text{OUT}} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & C_{\text{OUT}} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & C_{\text{OUT}} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline \textbf{Capacitiance} & V_{\text{DD}} & See Note 6 & 2.7 & 3.6 & V \\ \hline Capacitianc$		1	†		1		
$ \begin{array}{ c c c c c } \hline \textbf{INTERNAL REFERENCE} \\ \hline \textbf{REF Output Voltage} & VREF & 2.48 & 2.50 & 2.52 & V \\ \hline \textbf{REF Short-Circuit Current} & T_A = +25^{\circ}C & 15 & mA \\ \hline \textbf{REF Output Tempco} & TCVREF & & & & & & & & & & \\ \hline \textbf{REF Output Tempco} & TCVREF & & & & & & & & & & \\ \hline \textbf{Load Regulation} & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & & See Note 5; 0 to 0.75mA output load & 0.1 & 2.0 & mV/mA \\ \hline \textbf{Capacitive Bypass at REF} & & & & & & & & & & \\ \hline \textbf{DIGITAL INPUTS (SCLK, \overline{CS}, \overline{SHDN})} \\ \hline \textbf{Input High Voltage} & V_{INH} & & & & & & & & & \\ \hline \textbf{Input Low Voltage} & V_{INL} & & & & & & & & & \\ \hline \textbf{Input Hysteresis} & V_{HYST} & & & & & & & & & \\ \hline \textbf{Input Leakage} & I_{IN} & V_{INL} = 0V \text{ or } V_{INH} = V_{DD} & & & & & & \\ \hline \textbf{Input Capacitance} & C_{IND} & & & & & & & \\ \hline \textbf{DIGITAL OUTPUT (DOUT)} \\ \hline \textbf{Output Voltage Low} & V_{OL} & I_{SINK} = 5mA & & & & & & & \\ \hline \textbf{Output Voltage High} & V_{OH} & I_{SOURCE} = 0.5mA & V_{DD} - 0.5 & & & & V \\ \hline \textbf{Three-State Leakage Current} & I_{L} & V_{\overline{CS}} = +3V & & & & & & \\ \hline \textbf{POWER SUPPLY} \\ \hline \textbf{Positive Supply Voltage} & V_{DD} & See Note 6 & 2.7 & 3.6 & V \\ \hline \end{tabular}$				0		2.5	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		C _{INA}			10		pF
REF Short-Circuit Current $T_A = +25^{\circ}C$ 15mAREF Output TempcoTCVREF ± 15 ppm/°CLoad RegulationSee Note 5; 0 to 0.75mA output load0.12.0mV/mACapacitive Bypass at REF4.710 μ FDIGITAL INPUTS (SCLK, \overline{CS} , \overline{SHDN})Input High Voltage V_{INH} 2.0 V Input Low Voltage V_{INL} 0.8 V Input Hysteresis V_{HYST} 0.2 V Input Leakage I_{IN} $V_{INL} = 0V$ or $V_{INH} = V_{DD}$ ± 1 μ AInput Capacitance C_{IND} ± 1 μ ADIGITAL OUTPUT (DOUT) D ISINK = D INA D ISINK = D INA D INA D INAOutput Voltage Low V_{OL} $I_{SOURGE} = 0.5mA$ V_{OL} V INA V INAThree-State Leakage Current I_L $V_{CS} = +3V$ V INA V INA V INAPOWER SUPPLYPOWER SUPPLY V INA V INA V INA V INA V INAPositive Supply Voltage V DDSee Note 6 V INA V INA			1	1			
REF Output Tempco TCVREF See Note 5; 0 to 0.75mA output load 0.1 2.0 mV/mA	<u> </u>	VREF		2.48		2.52	
Load Regulation See Note 5; 0 to 0.75mA output load 0.1 2.0 mV/mA Capacitive Bypass at REF 4.7 10 μF DIGITAL INPUTS (SCLK, CS, SHDN) Input High Voltage V _{INH} 2.0 V Input Low Voltage V _{INL} 0.8 V Input Hysteresis V _{HYST} 0.2 V Input Leakage I _{IN} V _{INL} = 0V or V _{INH} = V _{DD} ±1 μA Input Capacitance C _{IND} 15 pF DIGITAL OUTPUT (DOUT) Output Voltage Low V _{OL} I _{SINK} = 5mA 0.4 V Output Voltage High V _{OH} I _{SOURCE} = 0.5mA V _{DD} - 0.5 V Three-State Leakage Current I _L V _{CS} = +3V ±10 μA Three-State Output Capacitance C _{OUT} V _{CS} = +3V 15 pF POWER SUPPLY Positive Supply Voltage V _{DD} See Note 6 2.7 3.6 V			$T_A = +25$ °C				
Capacitive Bypass at REF 4.7 10 μF DIGITAL INPUTS (SCLK, CS, SHDN) Input High Voltage V _{INH} 2.0 V Input Low Voltage V _{INL} 0.8 V Input Hysteresis V _{HYST} 0.2 V Input Leakage I _{IN} V _{INL} = 0V or V _{INH} = V _{DD} ±1 μA Input Capacitance C _{IND} 15 pF DIGITAL OUTPUT (DOUT) V _{OL} I _{SINK} = 5mA 0.4 V Output Voltage Low V _{OH} I _{SOURCE} = 0.5mA V _{DD} - 0.5 V Output Voltage High V _{OH} I _{SOURCE} = 0.5mA V _{DD} - 0.5 V Three-State Leakage Current I _L V _{CS} = +3V ±10 μA Three-State Output Capacitance C _{OUT} V _{CS} = +3V 15 pF POWER SUPPLY Positive Supply Voltage V _{DD} See Note 6 2.7 3.6 V		TCVREF					
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$ \begin{array}{ l c c c c c } \hline \text{Input High Voltage} & V_{\text{INH}} & 2.0 & V \\ \hline \text{Input Low Voltage} & V_{\text{INL}} & 0.8 & V \\ \hline \text{Input Hysteresis} & V_{\text{HYST}} & 0.2 & V \\ \hline \text{Input Leakage} & I_{\text{IN}} & V_{\text{INL}} = 0 \text{V or V}_{\text{INH}} = V_{\text{DD}} & \pm 1 & \mu \text{A} \\ \hline \text{Input Capacitance} & C_{\text{IND}} & 15 & pF \\ \hline \textbf{DIGITAL OUTPUT (DOUT)} & & & & & & & & & & & & & & & & & & &$				4.7		10	μF
$ \begin{array}{ l c c c c c c } \hline \text{Input Low Voltage} & V_{\text{INL}} & 0.8 & V \\ \hline \text{Input Hysteresis} & V_{\text{HYST}} & 0.2 & V \\ \hline \text{Input Leakage} & I_{\text{IN}} & V_{\text{INL}} = 0 \text{V or V}_{\text{INH}} = V_{\text{DD}} & & & \pm 1 & \mu \text{A} \\ \hline \text{Input Capacitance} & C_{\text{IND}} & & & & \pm 5 & pF \\ \hline \textbf{DIGITAL OUTPUT (DOUT)} & & & & & & 5 & pF \\ \hline \textbf{DIGITAL OUTPUT (DOUT)} & & & & & & & & & & & & & & & & & & &$)					
$ \begin{array}{ l c c c c c c c c c c c c c c c c c c $	Input High Voltage			2.0			
$ \begin{array}{ l c c c c c c c c c c c c c c c c c c $		V_{INL}				8.0	
$ \begin{array}{ l c c c c c c c c c c c c c c c c c c $		V_{HYST}			0.2		V
DIGITAL OUTPUT (DOUT) Output Voltage Low V_{OL} $I_{SINK} = 5mA$ 0.4 V Output Voltage High V_{OH} $I_{SOURCE} = 0.5mA$ $V_{DD} - 0.5$ V Three-State Leakage Current I_L $V_{\overline{CS}} = +3V$ ± 10 μA Three-State Output Capacitance C_{OUT} $V_{\overline{CS}} = +3V$ 15 pF POWER SUPPLY Positive Supply Voltage V_{DD} See Note 6 2.7 3.6 V		I _{IN}	$V_{INL} = 0V \text{ or } V_{INH} = V_{DD}$			±1	μΑ
Output Voltage Low V_{OL} $I_{SINK} = 5mA$ 0.4 V Output Voltage High V_{OH} $I_{SOURCE} = 0.5mA$ $V_{DD} - 0.5$ V Three-State Leakage Current I_L $V_{CS} = +3V$ ± 10 μA Three-State Output Capacitance C_{OUT} $V_{CS} = +3V$ 15 pF POWER SUPPLY Positive Supply Voltage V_{DD} See Note 6 2.7 3.6 V		C _{IND}			15		pF
Output Voltage High V_{OH} $I_{SOURCE} = 0.5 mA$ $V_{DD} - 0.5$ V Three-State Leakage Current I_L $V_{\overline{CS}} = +3V$ ± 10 μA Three-State Output Capacitance C_{OUT} $V_{\overline{CS}} = +3V$ 15 pF POWER SUPPLY Positive Supply Voltage V_{DD} See Note 6 2.7 3.6 V						-	
Three-State Leakage Current I_L $V_{\overline{CS}} = +3V$ ± 10 μA Three-State Output Capacitance C_{OUT} $V_{\overline{CS}} = +3V$ 15 pF POWER SUPPLY Positive Supply Voltage V_{DD} See Note 6 2.7 3.6 V	Output Voltage Low					0.4	
		V _{OH}		V _{DD} - 0.5			V
POWER SUPPLY Positive Supply Voltage V _{DD} See Note 6 2.7 3.6 V	Three-State Leakage Current	IL	$V_{CS} = +3V$			±10	
Positive Supply Voltage V _{DD} See Note 6 2.7 3.6 V	Three-State Output Capacitance	Соит	$V_{CS} = +3V$		15		pF
				•			•
	Positive Supply Voltage	V_{DD}	See Note 6	2.7		3.6	V
rositive Supply Current $ I_{DD} $ See Note I , $V_{DD} = +3.5$ V $ 2.5 3.5 MA$	Positive Supply Current	I _{DD}	See Note 7; V _{DD} = +3.6V		2.5	3.5	mA
Shutdown Supply Current $\frac{1}{SHDN}$ SCLK = V_{DD} , \overline{SHDN} = GND 2 10 μ A		1 .			2	10	μA
Power-Supply Rejection PSR $V_{DD} = +2.7V$ to 3.6V, midscale input ± 0.5 mV	11 7						



TIMING SPECIFICATIONS

 $V_{DD} = +2.7V$ to +3.6V, $T_A = -40^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted.

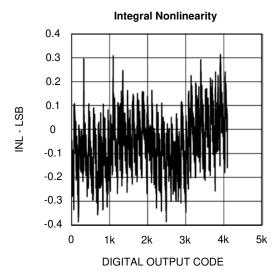
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
SCLK Period	t _{CP}		208			ns
SCLK Pulse-Width High	t _{CH}		83			ns
SCLK Pulse-Width Low	$t_{\sf CL}$		83			ns
CS Fall to SCLK Rise Setup	t _{CSS}		45			ns
SCLK Rise to CS Rise Hold	t _{CSH}		0			ns
SCLK Rise to CS Fall Ignore	t _{cso}		45			ns
CS Rise to SCLK Rise Ignore	t _{CS1}		45			ns
SCLK Rise to DOUT Hold	t _{DOH}	$C_{LOAD} = 20pF$	13			ns
SCLK Rise to DOUT Valid	t _{DOV}	$C_{LOAD} = 20pF$			100	ns
CS Rise to DOUT Disable	t _{DOD}	C _{LOAD} = 20pF; Refer to Figure 2	13		85	ns
CS Fall to DOUT Enable	t _{DOE}	C _{LOAD} = 20pF; Refer to Figure 1			85	ns
CS Pulse-Width High	t _{CSW}		100			ns

- Note 1: Tested at $V_{DD} = V_{DD(MIN)}$. Note 2: Relative accuracy is the deviation of the analog value at any code from its theoretical value after the full-scale range has been
- Note 3: Internal reference, offset, and reference errors nulled.
- Note 4: Conversion time is defined as the number of clock cycles multiplied by the clock period; clock has 50% duty cycle.
- Note 5: External load should not change during conversion for specified accuracy. Guaranteed specification limit of 2mV/mA because of production test limitations.
- Note 6: Electrical characteristics are guaranteed from V_{DD(MIN)} to V_{DD(MAX)}. For operations beyond this range, see Typical Operating Characteristics.
- Note 7: TSM1285 tested with 20pF on DOUT and f_{SCLK} = 4.8MHz, 0 to 3V. DOUT = full scale.

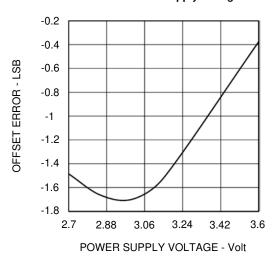


TYPICAL PERFORMANCE CHARACTERISTICS

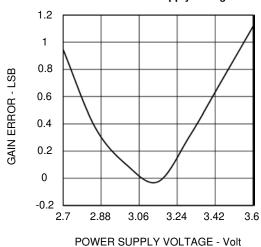
V_{DD} = +3V; f_{SCLK} = 4.8MHz; C_{LOAD} = 20pF; 4.7μF capacitor at REF; T_A = 25°C, unless otherwise noted.



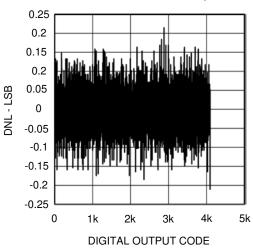




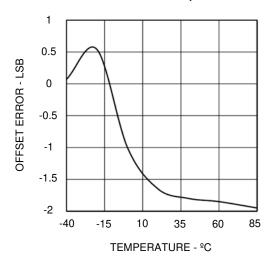
Gain Error vs Supply Voltage



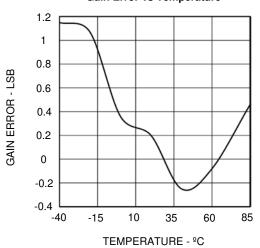
Differential Nonlinearity



Offset Error vs Temperature



Gain Error vs Temperature

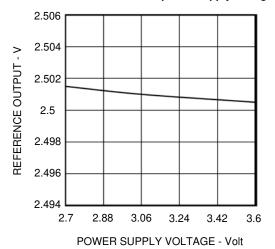




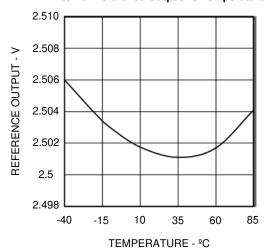
TYPICAL PERFORMANCE CHARACTERISTICS

V_{DD} = +3V; f_{SCLK} = 4.8MHz; C_{LOAD} = 20pF; 4.7μF capacitor at REF; T_A = 25°C, unless otherwise noted.

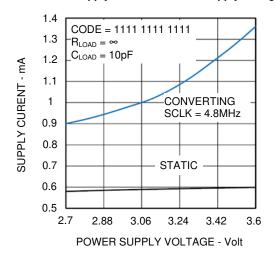
Internal Reference Output vs Supply Voltage



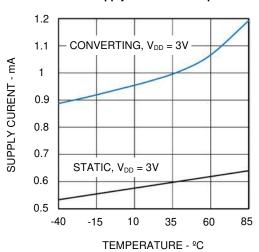
Internal Reference Output vs Temperature



Power Supply Current vs Power Supply Voltage



Power Supply Current vs Temperature



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PIN FUNCTIONS

PIN	NAME	FUNCTION			
1	VDD	Power Supply Voltage, +2.7V to +3.6V.			
2	AIN	Analog Signal Input; Unipolar, 0 to VREF input range.			
3	SHDN	Active-Low Shutdown Input. Toggling SHDN high-to-low powers down the TSM1285 and reduces the supply current to 2µA (typ).			
4	REF	Reference Voltage for Analog-to-Digital Conversion – an internal 2.5V reference output. Bypass with a good-quality 4.7µF capacitor.			
5	GND	Analog and Digital Ground. Connect the TSM1285's GND pin at one and only one point to the system analog ground plane.			
6	DOUT	Serial-Data Output. DOUT toggles state on SCLK's rising edge and is high impedance when CS is logic high.			
7	CS	Active-Low Chip Select. The $\overline{\text{CS}}$ signal initiates the conversion process on its falling edge. When the CS input is logic high, DOUT is high impedance.			
8	SCLK	Serial-Clock Input. The SCLK signal controls the conversion process and transfers output data at rates up to 4.8MHz.			

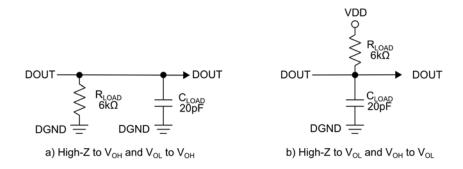


Figure 1: Output Loading Circuits for DOUT Enable Time (tdoe).

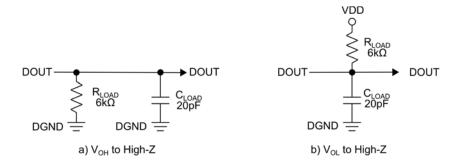


Figure 2: Output Loading Circuits for DOUT Disable Time (tDOD).



DESCRIPTION OF OPERATION

Converter Operation

The TSM1285 uses an input track-and-hold (T/H) and a successive-approximation register (SAR) circuitry to convert an analog input signal to a digital 12-bit output. No external-hold capacitor is needed for the track/hold circuit. Figure 3 illustrates the TSM1285 in its simplest configuration. The TSM1285 converts

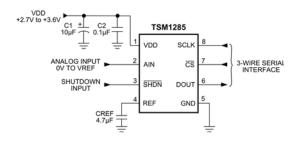


Figure 3: TSM1285 Typical Application Circuit.

input signals within the 0V to V_{REF} range in 3.3µs including the track-and-hold's acquisition time. The serial interface requires only three digital lines (SCLK, \overline{CS} , and DOUT) and provides an easy interface to microprocessors (µPs) and microcontrollers (µCs).

The TSM1285 has two operating modes: normal and shutdown. Toggling (or driving) the \overline{SHDN} pin low shuts down the ADCs and reduces supply current below 1 μ A when $V_{DD} \leq 3.6V$. Open-circuiting or toggling (or driving) the \overline{SHDN} pin high or places the ADCs into operational mode. Toggling the \overline{CS} pin to logic low initiates a conversion where the conversion result is available at DOUT in unipolar serial format. The serial data stream consists of three leading zeros followed by the data bits with the MSB first. All transitions on the DOUT pin occur within 20ns after the low-to-high transition of SCLK. Serial interface timing details of the TSM1285 are illustrated in Figures 8 and 9.

Analog Input

Figure 4 illustrates the sampling architecture of the

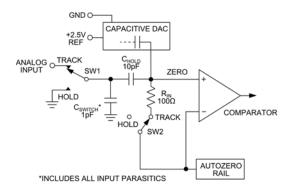


Figure 4: TSM1285 Equivalent Input Circuit Details.

analog-to-digital converter's comparator. The full-scale input voltage is set by the TSM1285's internal 2.5-V reference.

Track-and-Hold Operation

During track mode, the analog signal is acquired and stored on the internal hold capacitor. During hold mode, the track/hold switches SW1 and SW2 are opened thereby maintaining a constant input level to the converter's SAR subcircuit.

During the acquisition phase with SW1 and SW2 on TRACK, the input capacitor, C_{HOLD} , is charged to the analog input (AIN). Toggling the $\overline{\text{CS}}$ pin low causes the acquisition process to stop. At this instant, track/hold switches SW1 and SW2 are moved to HOLD position and the input side of C_{HOLD} is then switched to GND. Unbalancing Node ZERO at the comparator's input, the retained charge on C_{HOLD} represents a sample of the input signal applied to the converter.

In hold mode and to restore Node ZERO to 0V within the limits of the converter's 12- bit resolution, the output of the capacitive digital-to-analog converter (the CDAC) is adjusted during the remainder of the conversion cycle. In other words, the stored charge on CHOLD is transferred to the binary-weighted CDAC where it is converted into a digital representation of the analog input signal. At end of the conversion

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process, the input side of C_{HOLD} is switched back to AIN so as to be charged to the input signal again.

An ADC's acquisition time is function of how fast its input capacitance can be charged. If an input signal's driving-point source impedance is high, the acquisition time is lengthened and more time must be allowed between conversions. The acquisition time (taco) is the maximum time the ADC requires to acquire the signal and is also the minimum time needed for the signal to be acquired. The TSM1285's acquisition time is calculated from the following expression:

$$t_{ACQ} = 9 \times (R_S + R_{IN}) \times 10pF$$

where R_{IN} = 100 Ω (the TSM1285's internal track/hold switch resistance), R_S = the input signal's source impedance, and t_{ACQ} is never less than 625ns.

Because of the input structure of the TSM1285, sources with output impedances of $1k\Omega$ or less do not affect significantly the AC performance of the TSM1285. The TSM1285 can still be used in applications where the source impedance is higher so long as a $0.01\mu F$ capacitor is connected between the analog input and GND. Limiting the ADC's input signal bandwidth, the use of an external, input capacitor forms an RC filter with the input's source impedance.

Input Bandwidth Considerations

Since the TSM1285's input track-and-hold circuit exhibits a 10 MHz small-signal bandwidth, it is possible to measure periodic signals and to digitize high-speed transient events with signal bandwidths higher than the TSM1285's sampling rate by using undersampling techniques. To avoid the aliasing of high-frequency signals into the frequency band of interest, the use of external anti-alias filter circuits (discrete or integrated) is recommended. The time constant of the external anti-alias filter should be set so as not to interfere with the desired signal bandwidth.

Analog Input Protection

The TSM1285 incorporates internal protection diodes that clamp the analog input between V_{DD} and GND. These internal protection diodes allow the AIN pin to swing from GND - 0.3V to V_{DD} + 0.3V without causing

damage to the TSM1285. However, for accurate conversions near full scale, the input signal must not exceed V_{DD} by more than 50mV or be lower than GND by 50mV.

If the analog inputs can exceed 50mV beyond the supplies, then the current in the forward-biased protection diodes should be limited to less than 2mA since large fault currents can affect conversion results.

Internal Reference Considerations

The TSM1285 has an internal voltage reference that is factory-trimmed to 2.5V. The internal reference output is connected to the REF pin and is also connected to the ADC's internal CDAC. The REF output can be used as a reference voltage source for other components external to the ADC and can source up to 750µA. To maintain conversion accuracy to within 1 LSB, a 4.7µF capacitor from the REF pin to GND is recommended. While largervalued capacitors can be used to further reduce reference wide-band noise, larger capacitor values can increase the TSM1285's wake-up time when exiting from shutdown mode (see the "Using SHDN to Reduce Operating Supply Current" section for more information). When in shutdown (that is, when SHDN = 0), the TSM1285's internal 2.5-V reference is disabled.

Serial Digital Interface

Initialization after Power-Up and Starting a Conversion

If the \overline{SHDN} pin is not driven low upon an initial, cold-start condition, it may take up to 2.5ms for a fully-discharged 4.7µF reference bypass capacitor to provide adequate charge for specified conversion accuracy. As a result, conversions should not be initiated during this reference capacitor charge-up delay. To initiate a conversion, the \overline{CS} pin is toggled (or driven) low. At the \overline{CS} 's falling edge, the TSM1285's internal track-and-hold is placed in hold mode and a conversion is initiated. Data can then be transferred out of the ADC using an external serial clock.



Using the ADC's SHDN to Reduce Operating Supply Current

Power consumption can be reduced significantly by turning off the TSM1285 in between conversions.

Figure 5: TSM1285 Supply Current vs Conversion Rate

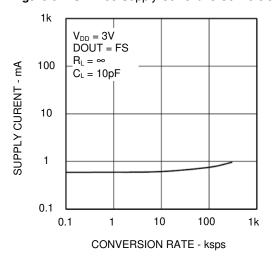


Figure 5 illustrates the TSM1285's average supply current versus conversion rate. The wake-up delay time (t_{WAKE}) is the time from when the \overline{SHDN} pin is deasserted to the time when a conversion may be initiated (Refer to Figure 6). This delay time depends on how long the ADC was in shutdown (Refer to Figure 7) because the external $4.7\mu F$ reference bypass capacitor is discharged slowly when $\overline{SHDN}=0$.

Timing and Control Details

The $\overline{\text{CS}}$ and SCLK digital inputs control the TSM1285's conversion-start and data-read operations. The ADC's serial-interface operations are illustrated in Figures 8 and 9.

A $\overline{\text{CS}}$ high-to-low transition initiates the conversion sequence - the input track-and-hold samples the input signal level, the ADC begins to convert, and the DOUT pin changes state from high impedance to logic low. The external SCLK signal is used to drive the conversion process and is also used to transfer the converted data out of the ADC as each bit of conversion is determined.

The SCLK signal transfers data after a low-to-high transition of the third (3rd) SCLK pulse. After each subsequent SCLK rising edge, transitions on the DOUT pin occur in 20ns. The third rising clock edge produces the MSB of the conversion at DOUT, followed by the remaining bits. Since there are twelve data bits and three leading zeros, at least fifteen rising clock edges are needed to transfer the entire data stream. Extra SCLK pulses occurring after the conversion result has been completely transferred out and, before to a new, low-to-high transition on $\overline{\text{CS}}$, produce a string trailing zeros at DOUT. In addition, the extra SCLK pulses have no effect on converter operation.

Minimum conversion cycle time can be accomplished by: (a) toggling the \overline{CS} pin high after reading the conversion result's LSB; and (b), after the specified minimum time defined by t_{CS} has elapsed, toggling the \overline{CS} pin low again to initiate the next conversion.

Output Data Coding and Transfer Function

Conversion results at the TSM1285's DOUT pin are straight binary data. Figure 10 illustrates the nominal transfer function where code transitions occur halfway between successive integer LSB values. If $V_{REF} = +2.500V$, then 1 LSB = 610 μ V or 2.500V/4096.

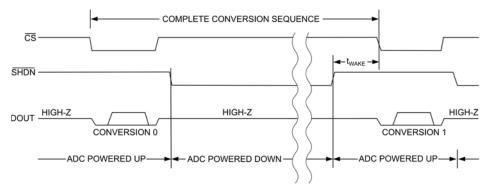
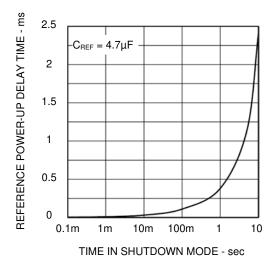


Figure 6: TSM1285 Shutdown Operation.

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Figure 7: TSM1285 Reference Power-Up Delay vs Duration in Shutdown Mode



APPLICATIONS INFORMATION

Connection to Industry-Standard Serial Interfaces

The TSM1285's serial interface is fully compatible with SPI/QSPI and MICROWIRE standard serial interfaces (Refer to Figure 11). For serial interface operation with these standards, the CPU's serial interface should be set to master mode so the CPU then generates the serial clock. Second, the CPU's serial clock should be configured to operate up to 4.8MHz. The process to configure the serial clock and data transfer operation is as follows:

 $\overline{\text{CS}}$ pin is driven low to start a conversion. DOUT transitions from high impedance to logic low. The SCLK polarity should be low to start the conversion process correctly.

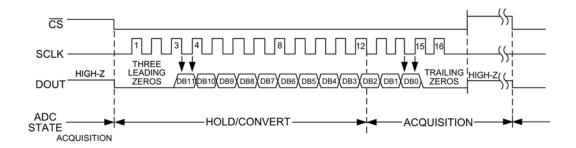


Figure 8: TSM1285 Serial Interface Timing Sequence

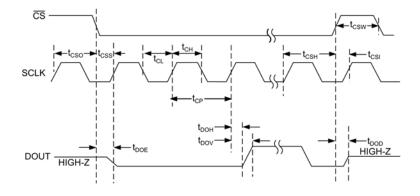


Figure 9: TSM1285 Serial Interface Timing Specifications in Detail.

2) Next, SCLK is activated for a minimum of 15 SCLK cycles where the first two SCLKs produce zeros at the DOUT pin. Data at DOUT is formatted MSB first

and DOUT transitions occur 20ns after the third (3rd) SCLK low-to-high transition. Once the low-to-high SCLK transition has occurred, data is valid at DOUT



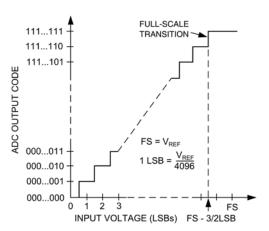


Figure 10: ADC Unipolar Transfer Function for Straight Binary Digital Data.

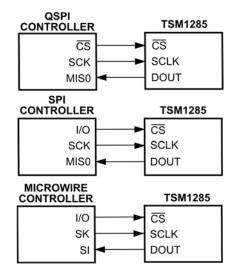


Figure 11: TSM1285 Circuit Connections to Industry-Standard Serial Interfaces.

according to the t_{DOV} (SCLK Rise to DOUT Valid) timing specification. Valid output data can then be transferred into μP or μCs on SCLK low-to-high transitions.

3) At or after the 15th SCLK low-to-high transition, the $\overline{\text{CS}}$ pin can be toggled high to halt the transfer process. If the $\overline{\text{CS}}$ pin remains low and the SCLK is still active, trailing zeros are transferred out after the LSB.

4) Once the $\overline{\text{CS}}$ pin is held at logic high for at least tos, a new conversion cycle is started when the $\overline{\text{CS}}$ pin is toggled low. If a conversion is aborted by toggling the $\overline{\text{CS}}$ pin high before the current conversion has completed, a new conversion cycle can only be started after a the ADC has acquired the signal (t_{ACO}).

The $\overline{\text{CS}}$ pin must be held low and SCLK active until all data bits are transferred out of the ADC. As shown in Figure 8, data can be transferred in two 8-bit bytes or continuously. The bytes contain the result of the conversion padded with three leading 0s in the first 8-bit byte and 1 trailing 0 in the second 8-bit byte.

SPI and MICROWIRE Interface Details

When using an SPI or MICROWIRE interface, setting [CPOL:CPHA] = [0:0] configures the microcontroller's serial clock and sampling edge for the TSM1285. The conversion commences on a high-to-low transition of the $\overline{\text{CS}}$ pin. The DOUT pin transitions from a high-impedance state to a logic low, indicating a conversion is in progress. Two consecutive 1-byte data reads are required to transfer the full 12-bit result from the ADC. DOUT output data transitions occur on the SCLK's low-to-high transition and are transferred into the downstream microcontroller on the SCLK's low-to-high transition.

The first byte contains three leading 0s and then five bits of the conversion result. The second byte contains the remaining seven bits of the conversion result and one trailing zero. Refer to Figure 11 for the circuit connections and to Figure 12 for all timing details.

QSPI Details

Using a QSPI microcontroller, setting [CPOL:CPHA] = [0:1] configures the microcontroller's serial clock and sampling edge for the TSM1285. Unlike the SPI, which requires two 1-byte reads to transfer all 12 bits of data from the ADC, the QSPI allows a minimum number of clock cycles necessary to transfer data from the ADC to the microcontroller. Thus, the TSM1285 requires 15 SCLK clock cycles from the microcontroller to transfer the 12 bits of data with no trailing zeros. As shown in Figure 13, the conversion results contain two leading 0s followed by the MSB-first-formatted, 12-bit data stream.

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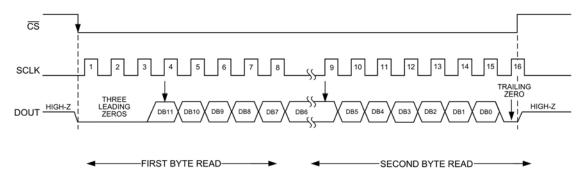


Figure 12: SPI/MICROWIRE-TSM1285 Serial Interface Timing Details with [CPOL:CPHA] = [0:0].

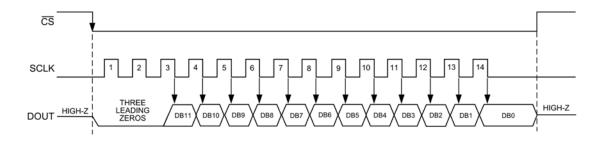


Figure 13: QSPI-TSM1285 Serial Interface Timing Details with [CPOL:CPHA] = [0:1].

PCB Layout, Ground Plane Management, and Capacitive Bypassing

For best performance, printed circuit boards should always be used and wire-wrap boards are not recommended. Good PC board layout techniques ensure that digital and analog signal lines are kept separate from each other, analog and digital

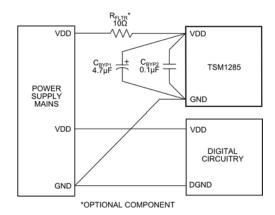


Figure 14: Recommended Power Supply Bypassing and Star Ground Configuration.

(especially clock) lines are not routed parallel to one another, and high-speed digital lines are not routed underneath the ADC package.

A recommended system ground connection is illustrated in Figure 14. A single-point analog ground (star ground point) should be created at the ADC's GND and separate from the logic ground. All analog grounds as well as the ADC's GND pin should be connected to the star ground. No other digital system ground should be connected to this ground. For lowest-noise operation, the ground return to the star ground's power supply should be low impedance and as short as possible.

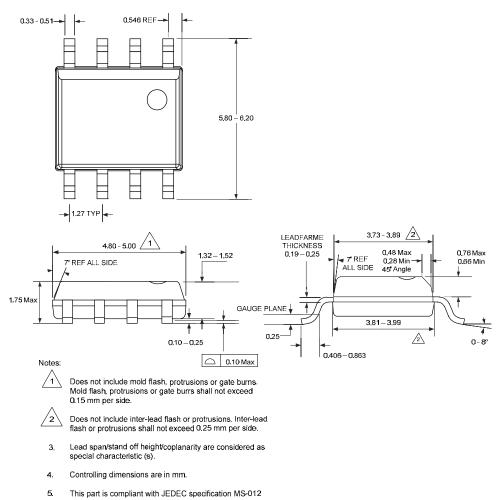
High-frequency noise on the V_{DD} power supply may affect the ADC's high-speed comparator. Therefore, it is necessary to bypass the V_{DD} supply pin to the star ground with 0.1µF and 1µF capacitors in parallel and placed close to the ADC's Pin 1. Component lead lengths should be very short for optimal supply-noise rejection. If the power supply is very noisy, an optional $10\text{-}\Omega$ resistor can be used in conjunction with the bypass capacitors to form a low-pass filter as shown in Figure 14.



PACKAGE OUTLINE DRAWING

8-Pin SOIC Package Outline Drawing

(N.B., Drawings are not to scale)



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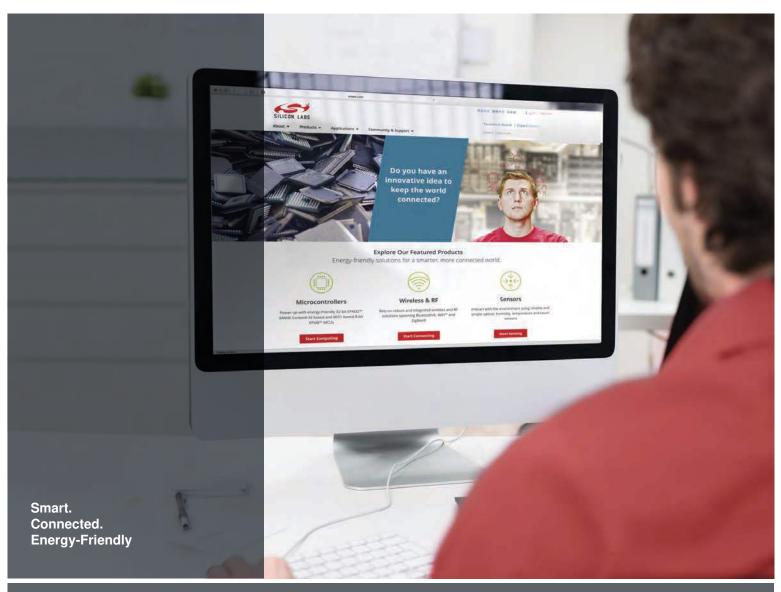
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